



2110MHz-2170MHz, 160W, 28V High Power RF LDMOS FETs

Description

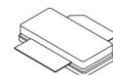
The ITCH22161B2 is a 160-watt, internally matched LDMOS FET, designed for multicarrier WCDMA/PCS/DCS/LTE base station and ISM applications with frequencies from 2000 to 2200 MHz. It Can be used in Class AB/B and Class C for all typical cellular base station modulation formats.

•Typical Performance (On Innegration fixture with device soldered):

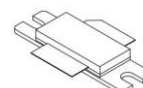
VDD = 28 Volts, IDQ = 800 mA, Pulse CW, Pulse Width=20 us, Duty cycle=10% .

Frequency (MHz)	Gp @ P _{OUT} =48dBm (dB)	P _{-1dB} (dBm)	P _{-3dB} (dBm)	η_D @P ₋₃ (%)
2110	17.5	52.5	53.3	56
2140	17.5	52.2	53.1	56
2170	17.5	51.8	52.9	56

ITCH22161B2



ITCH22161B2E



•Typical Single-Carrier W-CDMA Performance (On Test Fixture with device soldered):

V_{DD}=28Volts, IDQ = 800 mA, P_{OUT}= 46dBm Avg., IQ Magnitude Clipping, Channel Bandwidth = 3.84 MHz, Input Signal PAR = 10.5 dB @ 0.01% Probability on CCDF.

Frequency	P _{OUT} (dBm)	Gp (dB)	η_D (%)	ACPR _{5M} (dBc)
2110 MHz	46	17.2	31	-30.5
2140 MHz	46	17.2	31	-31.0
2170 MHz	46	17.2	31	-31.8

Features

- High Efficiency and Linear Gain Operations
- Integrated ESD Protection
- Internally Matched for Ease of Use
- Excellent thermal stability, low HCI drift
- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation
- Pb-free, RoHS-compliant

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain--Source Voltage	V _{DSS}	70	Vdc
Gate--Source Voltage	V _{GS}	-10 to +10	Vdc
Operating Voltage	V _{DD}	+32	Vdc
Storage Temperature Range	T _{stg}	-65 to +150	°C
Case Operating Temperature	T _c	+150	°C
Operating Junction Temperature	T _j	+225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case T _c = 85°C, T _j =200°C, DC test	R _{θJC}	0.38	°C/W

**Table 3. ESD Protection Characteristics**

Test Methodology	Class
Human Body Model (per JESD22--A114)	Class 2

Table 4. Electrical Characteristics (TA = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
DC Characteristics					
Drain-Source Breakdown Voltage (V _{GS} =0V; I _D =1mA)	V _{DSS}	65	70		V
Zero Gate Voltage Drain Leakage Current (V _{DS} = 28 V, V _{GS} = 0 V)	I _{DSS}			10	μA
Gate--Source Leakage Current (V _{GS} = 10 V, V _{DS} = 0 V)	I _{GSS}			1	μA
Gate Threshold Voltage (V _{DS} = 28V, I _D = 600 μA)	V _{GS(th)}		1.8		V
Gate Quiescent Voltage (V _{DD} = 28 V, I _{DQ} = 800 mA, Measured in Functional Test)	V _{GS(Q)}	2.2	2.7	3.2	V

Functional Tests (On Innogrations demo, 50 ohm system) :V_{DD} = 28 Vdc, I_{DQ} = 800 mA, f = 2110 MHz, Pulse CW, Pulse Width=20 us, Duty cycle=10% .

Power Gain @ P _{OUT} =48dBm	G _p		17.5		dB
1 dB Compression Point	P _{-1dB}		52.5		dBm
3dB Compression Point	P _{-3dB}		53.3		dBm
Drain Efficiency@P3dB	η _D		54.2		%
Input Return Loss	IRL		-7		dB

Load Mismatch (In Innogrations Test Fixture, 50 ohm system): V_{DD} = 28 Vdc, I_{DQ} = 800 mA, f = 2110 MHz

VSWR 10:1 at 200W pulse CW Output Power	No Device Degradation
---	-----------------------

TYPICAL CHARACTERISTICS

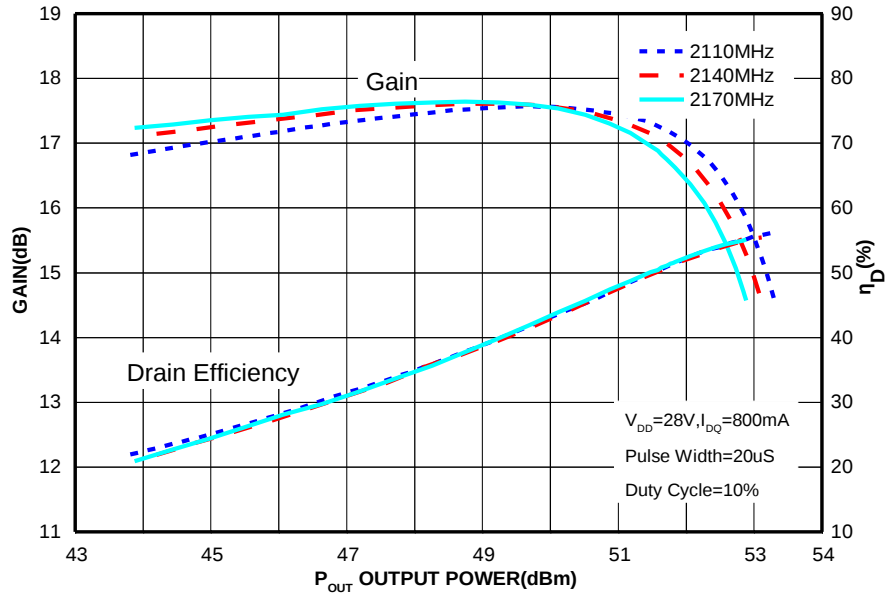


Figure 1. Power gain and drain efficiency as function of
Pulse output power

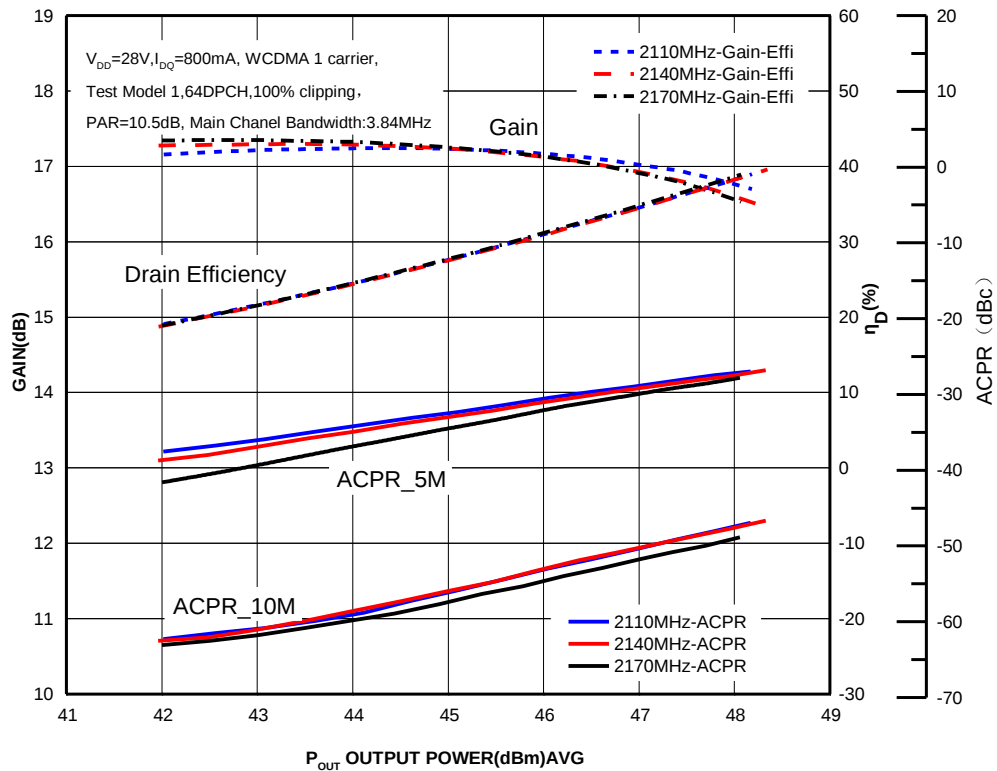
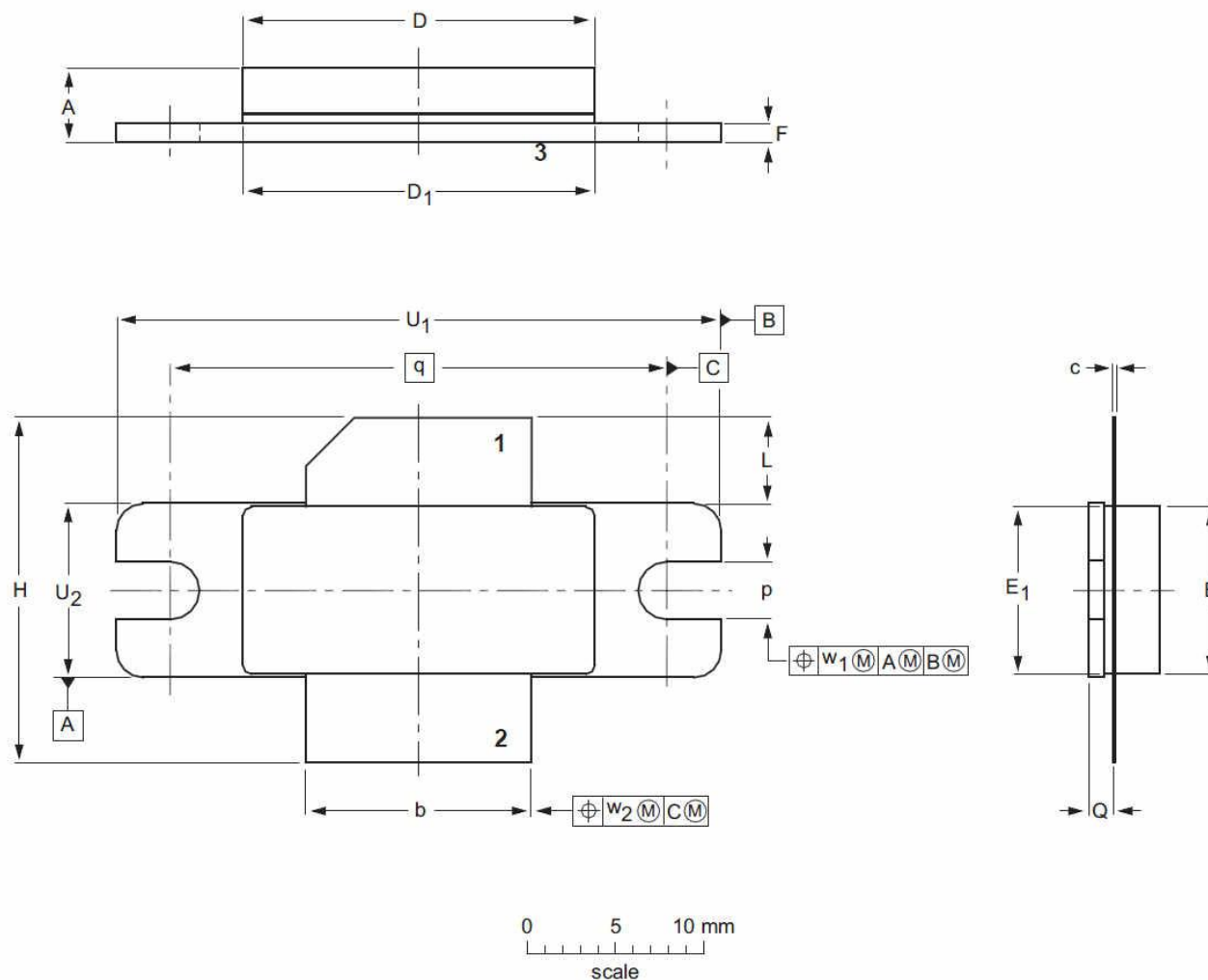


Figure 2. Single-Carrier WCDMA Power gain and drain efficiency and
ACPR at 5 MHz and at 10 MHz as function of average output power



Package Outline

Flanged ceramic package; 2 mounting holes; 2 leads (1—DRAIN、2—GATE、3—SOURCE)

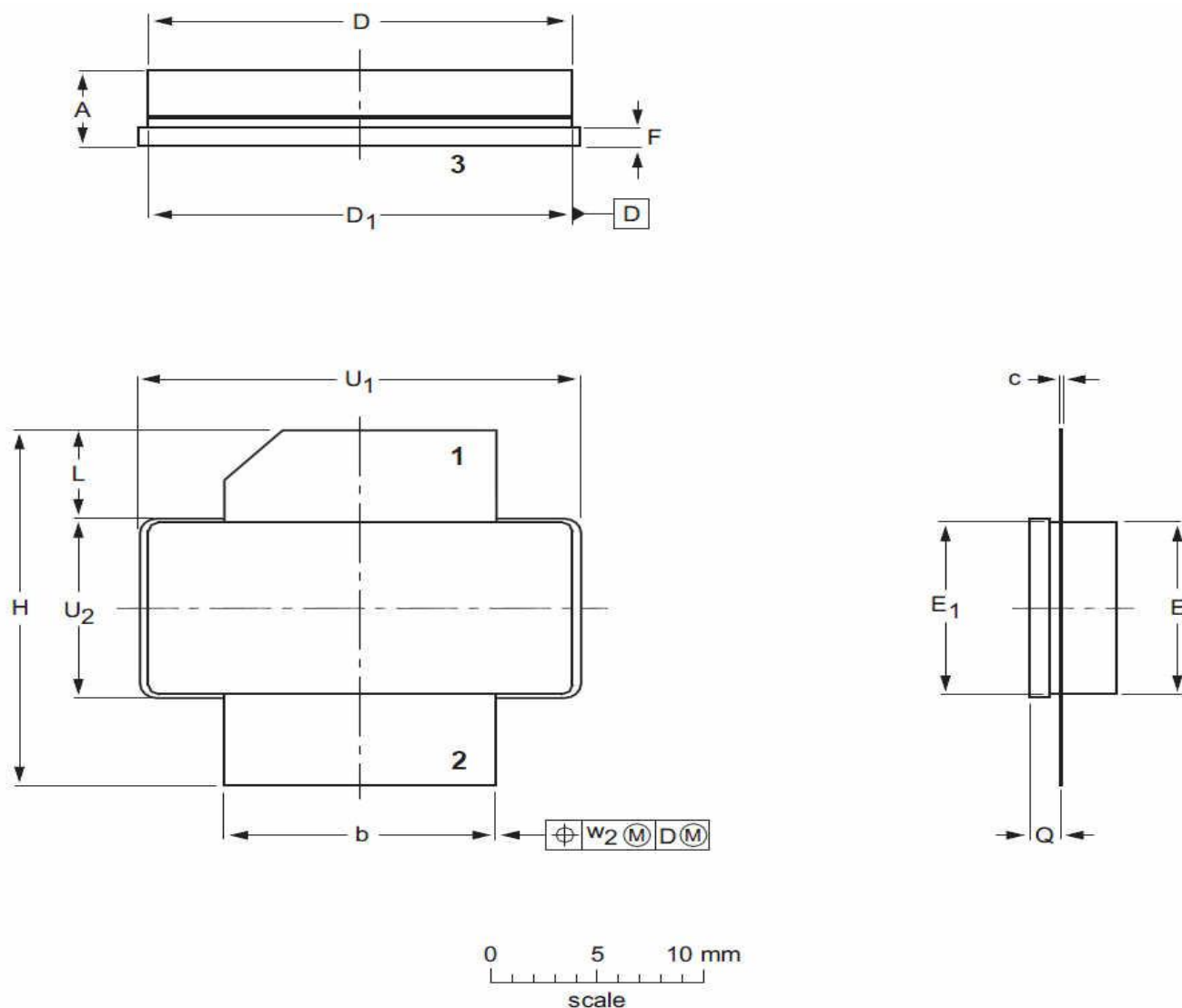


UNIT	A	b	c	D	D ₁	E	E ₁	F	H	L	p	Q	q	U ₁	U ₂	W ₁	W ₂
mm	4.72	12.83	0.15	20.02	19.96	9.50	9.53	1.14	19.94	5.33	3.38	1.70	27.94	34.16	9.91	0.25	0.51
	3.43	12.57	0.08	19.61	19.66	9.30	9.25	0.89	18.92	4.32	3.12	1.45		33.91	9.65		
inches	0.186	0.505	0.006	0.788	0.786	0.374	0.375	0.045	0.785	0.210	0.133	0.067	1.100	1.345	0.390	0.01	0.02
	0.135	0.495	0.003	0.772	0.774	0.366	0.364	0.035	0.745	0.170	0.123	0.057		1.335	0.380		

OUTLINE VERSION	REFERENCE			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
PKG-B2E					03/12/2013



Earless flanged ceramic package; 2 leads (1—DRAIN、2—GATE、3—SOURCE)



UNIT	A	b	c	D	D ₁	E	E ₁	F	H	L	Q	U ₁	U ₂	W ₂
mm	4.72	12.83	0.15	20.02	19.96	9.50	9.53	1.14	19.94	5.33	1.70	20.70	9.91	0.25
	3.43	12.57	0.08	19.61	19.66	9.30	9.25	0.89	18.92	4.32	1.45	20.45	9.65	
inches	0.186	0.505	0.006	0.788	0.786	0.374	0.375	0.045	0.785	0.210	0.067	0.815	0.390	0.010
	0.135	0.495	0.003	0.772	0.774	0.366	0.364	0.035	0.745	0.170	0.057	0.805	0.380	

OUTLINE VERSION	REFERENCE			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
PKG-B2					03/12/2013



Revision history

Table 5. Document revision history

Date	Revision	Datasheet Status
2017/09/04	Rev 1.0	Preliminary Datasheet

Disclaimers

Specifications are subject to change without notice. Innogrations believes the information contained within this data sheet to be accurate and reliable. However, no responsibility is assumed by Innogrations for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Innogrations. Innogrations makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose. "Typical" parameters are the average values expected by Innogrations in large quantities and are provided for information purposes only. These values can and do vary in different applications and actual performance can vary over time. All operating parameters should be validated by customer's technical experts for each application. Innogrations products are not designed, intended or authorized for use as components in applications intended for surgical implant into the body or to support or sustain life, in applications in which the failure of the Innogrations product could result in personal injury or death or in applications for planning, construction, maintenance or direct operation of a nuclear facility. For any concerns or questions related to terms or conditions, pls check with Innogrations and authorized distributors

Copyright © by Innogrations (Suzhou) Co.,Ltd.